

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re divisional patent application of 09/824,672 filed on April 4, 2001

In re patent application of

Mariko Makabe, et al

Serial No.: Not Yet Assigned **Group Art Unit:** Not Yet Assigned

Filing Date: Concurrently Herewith **Examiner:** Unknown

For: HIGH-PERFORMANCE MOS TRANSISTOR OF LDD STRUCTURE HAVING A
GATE INSULATING FILM WITH A NITRIDE CENTRAL PORTION AND
OXIDE END PORTIONS

Commissioner for Patents
Alexandria, VA 22313-1450

PRELIMINARY AMENDMENT

Sir:

Prior to examination on the merits and calculation of the filing fee, please amend the
above-identified application as follows:

INTRODUCTORY COMMENTS

Claims 1-11 have been canceled to allow prosecution of claims 12-19. No new matter
has been added.

Docket No. NEC01P065-SYa

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AMENDMENTS TO THE TITLE:

Please amend the title to read as follows:

HIGH-PERFORMANCE MOS TRANSISTOR OF LDD STRUCTURE HAVING A
GATE INSULATING FILM WITH A NITRIDE CENTRAL PORTION AND OXIDE END
PORTIONS